

Excellent Integrated System Limited

Stocking Distributor

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Vishay/Siliconix SI7358ADP-T1-E3

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Si7358ADP

Vishay Siliconix

N-Channel 30-V (D-S) MOSFET

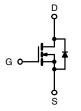
PRODUCT SUMMARY					
V _{DS} (V)	$R_{DS(on)}(\Omega)$	$R_{DS(on)}(\Omega)$ $I_{D}(A)$ $Q_{g}(T_{g})$			
30	0.0042 at V _{GS} = 10 V	23	30.5		
30	0.0059 at $V_{GS} = 4.5 \text{ V}$	20	30.5		

FEATURES

- · Halogen-free available
- TrenchFET® Power MOSFET
- Optimized for "Low Side" Synchronous **Rectifier Operation**
- New Low Thermal Resistance PowerPAK® Package with Low 1.07 mm Profile
- 100 % R_q Tested

APPLICATIONS

- DC/DC Converters
- Synchronous Rectifiers



N-Channel MOSFET

À	
6.15 mm	5.15 mm
	35 35
8000	

PowerPAK SO-8

Bottom View

Ordering Information: Si7358ADP-T1-E3 (Lead (Pb)-free)

Si7358ADP-T1-GE3 (Lead (Pb)-free and Halogen-free)

ABSOLUTE MAXIMUM RATINGS	T _A = 25 °C, unles	ss otherwise n	oted		
Parameter		Symbol	10 s	Steady State	Unit
Drain-Source Voltage		V_{DS}	30		V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T _{.1} = 150 °C) ^a	T _A = 25 °C	I _D	23	14	
Continuous Diam Current (TJ = 150 C)	T _A = 70 °C		18	11	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	60		Α
Continuous Source Current (Diode Conduction) ^a		I _S	4.5	1.6	
Avalanche Current	L = 0.1 mH	I _{AS}	50		
Maximum Dawar Dissinationa	T _A = 25 °C	P _D	5.4	1.9	W
Maximum Power Dissipation ^a	T _A = 70 °C		3.4	1.2	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150		°C
Soldering Recommendations (Peak Temperature) ^{b, c}			2	260	O

THERMAL RESISTANCE RATINGS						
Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^a	t ≤ 10 s	R _{thJA}	18	23		
Maximum Junction-to-Ambient	Steady State		50	65	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	1.0	1.5		

Notes:

- a. Surface Mounted on 1" x 1" FR4 board.
- b. See Solder Profile (http://www.vishay.com/ppg?73257). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework Conditions: manual soldering with a soldering iron is not recommended for leadless components.

Document Number: 73161 S-80438-Rev. E, 03-Mar-08

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Datasheet of SI7358ADP-T1-E3 - MOSFET N-CH 30V 14A PPAK SO-8

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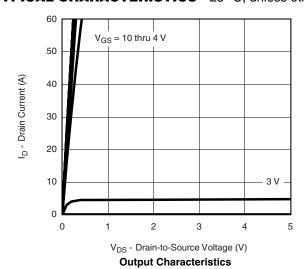
SPECIFICATIONS T _J = 25 °C, unless otherwise noted								
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit		
Static			T	1	1			
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1.0		3.0	V		
Gate-Body Leakage	I _{GSS}	20 00		± 100	nA			
Zero Gate Voltage Drain Current	lace	V _{DS} = 30 V, V _{GS} = 0 V			1			
	I _{DSS}	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	μΑ		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	30			Α		
	В	V _{GS} = 10 V, I _D = 23 A		0.0032	0.0042			
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 4.5 \text{ V}, I_D = 20 \text{ A}$		0.0045	0.0059	Ω		
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 23 A	= 23 A			S		
Diode Forward Voltage ^a	V _{SD}	I _S = 4.5 A, V _{GS} = 0 V		0.75	1.1	V		
Dynamic ^b	•			•				
Input Capacitance	C _{iss}			4650		pF		
Output Capacitance	C _{oss}	$V_{DS} = 15 \text{ V}, V_{SS} = 0 \text{ V}, f = 1 \text{ kHz}$		880				
Reverse Transfer Capacitance	C _{rss}			390				
Total Gate Charge	Qg			30.5	40			
Gate-Source Charge	Q_{gs}	V _{DS} = 15 V, V _{GS} = 4.5 V, I _D = 23 A		12.5		nC		
Gate-Drain Charge	Q_{gd}			10		1		
Gate Resistance	R_g		0.5	1.0	1.5	Ω		
Turn-On Delay Time	t _{d(on)}			21	35			
Rise Time	t _r	V_{DD} = 15 V, R_L = 15 Ω		10	20	. ns		
Turn-Off Delay Time	t _{d(off)}	$I_D\cong$ 1 A, V_{GEN} = 10 V, R_G = 6 Ω		83	130			
Fall Time	t _f			27	45			
Source-Drain Reverse Recovery Time	t _{rr}	$I_F = 2.9 \text{ A}, \text{ di/dt} = 100 \text{ A/}\mu\text{s}$		50	80			

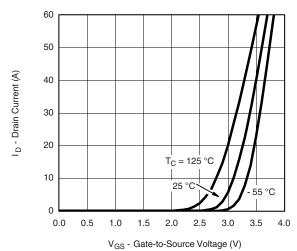
Notes:

- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Transfer Characteristics





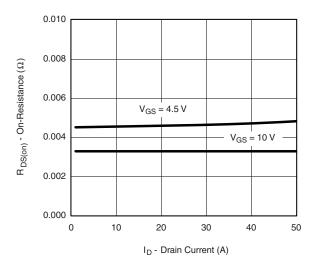
V_{GS} - Gate-to-Source Voltage (V)

Is-Source Current (A)

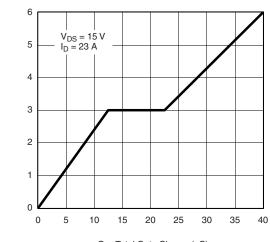
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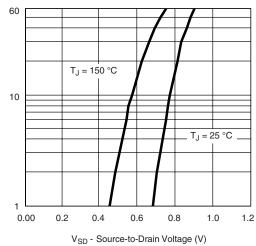
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



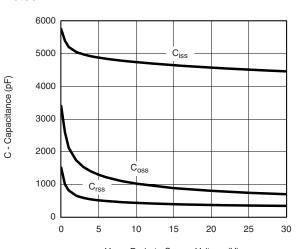
On-Resistance vs. Drain Current



 Q_g -Total Gate Charge (nC) **Gate Charge**

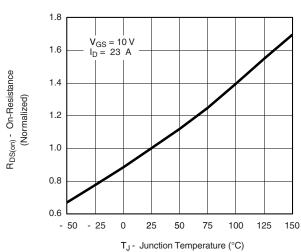


Source-Drain Diode Forward Voltage

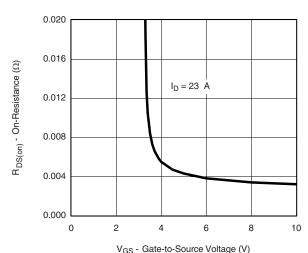


 $V_{\mbox{\footnotesize{DS}}}$ - Drain-to-Source Voltage (V)





On-Resistance vs. Junction Temperature



On-Resistance vs. Gate-to-Source Voltage

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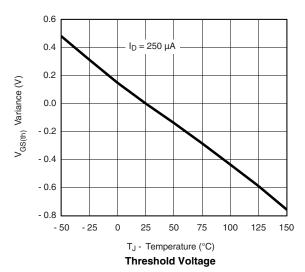


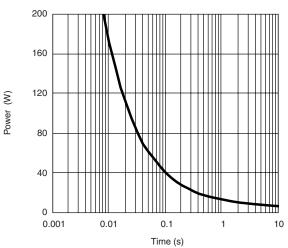
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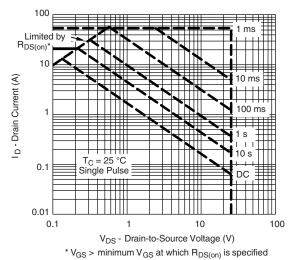
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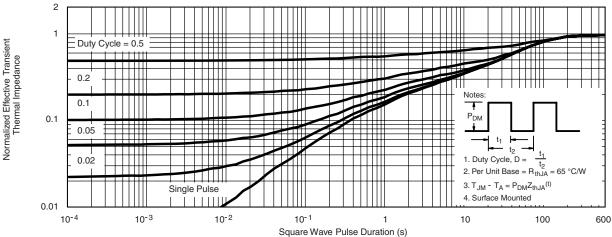




Single Pulse Power, Junction-to-Ambient



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

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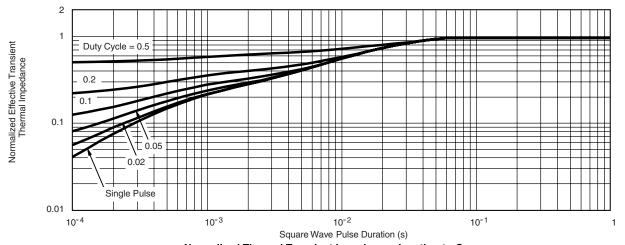
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Si7358ADP

Vishay Siliconix

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see http://www.vishay.com/ppg?73161.

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Revision: 13-Jun-16 1 Document Number: 91000